TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

# 2SC3265

## Low Frequency Power Amplifier Applications Power Switching Applications

- High DC current gain:  $h_{FE}$  (1) =  $100 \sim 320$
- Low saturation voltage: VCE (sat) = 0.4 V (max) (IC = 500 mA, IB = 20 mA)
- Complementary to 2SA1298

### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	30	V
Collector-emitter voltage	V <sub>CEO</sub>	25	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	800	mA
Base current	I <sub>B</sub>	160	mA
Collector power dissipation	PC	200	mW
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

# Unit: mm 2.5 + 0.5 2.5 - 0.3 1.5 + 0.25 1.

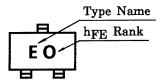
### Weight: 0.012 g (typ.)

### **Electrical Characteristics (Ta = 25°C)**

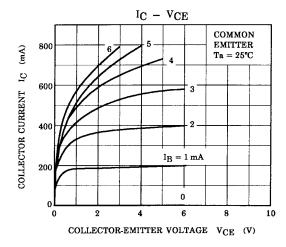
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 30 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	_	_	0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = 10 \text{ mA}, I_B = 0$	25	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	I <sub>E</sub> = 0.1 mA, I <sub>C</sub> = 0	5	_	_	V
DC current gain	h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 100 mA	100	_	320	
	h <sub>FE (2)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 800 mA	40	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_C = 500 \text{ mA}, I_B = 20 \text{ mA}$	_	_	0.4	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 10 mA	0.5	_	0.8	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10 mA	_	120	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	13	_	pF

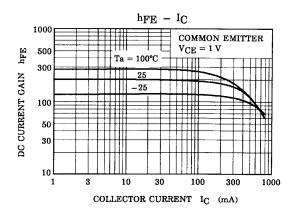
Note: hFE (1) classification O: 100~200, Y: 160~320

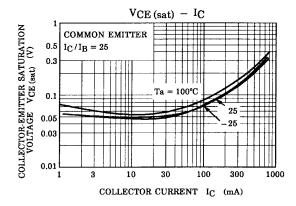
### Marking

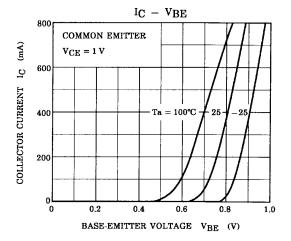


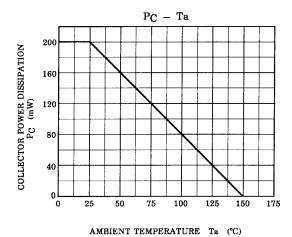
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